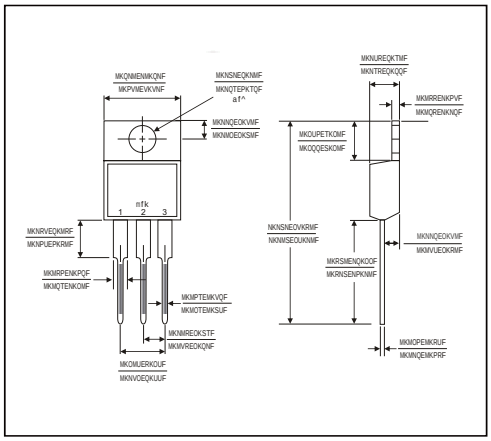
220AB

Features

ŏRDS(ON) =3.8 @VGS =10V .
ŏLow gate charge (typical 9.0 nC).
ŏLow Crss (typical 5.0 pF).
ŏFast switching capability.
ŏAvalanche energy specified Improved dv/dt capability.
ŏN-Channel MOSFET

:TO-2



Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Gate-Source Voltage	V_{GSS}	±30	V
Drain Current - Continuous (T_C = 25 ℃) Continuous (T_C = 100 ℃)	I_D	2.0 1.26	A
Drain Current - Pulsed * 1	I_{DP}	8.0	A
Single Pulsed Avalanche Energy * 2	E_{AS}	140	mJ
Avalanche Current * 1	I_{AR}	2.0	A
Repetitive Avalanche Energy * 1	E_{AR}	4.5	mJ
Peak Diode Recovery dv/dt * 3	dv/dt	4.5	V/ns
Power Dissipation (T_C = 25℃) Derate above 25℃	P_D	44 0.36	W W/ ℃
Operating and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	℃
Maximum lead temperature for soldering purposes,1/8" from case for 5 seconds	T_L	300	℃
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4	℃/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	54	℃/W

* 1. Repetitive Rating : Pulse width limited by maximum junction temperature.

* 2. L = 64mH, I_{AS} = 2.0A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25℃

* 3. I_{SD} ≤ 2.4A, di/dt ≤ 200A/□s, V_{DD} ≤ BV_{DSS}, Starting T_J = 25℃

℃